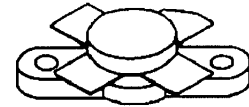


MS1051

RF & MICROWAVE TRANSISTORS HF SSB APPLICATIONS

Features

- 30 MHz
- 12.5 VOLTS
- P_{OUT} = 100 WATTS
- G_{PE} = 12.0 dB MINIMUM
- IMD = -30 dBc
- GOLD METALLIZATION
- COMMON EMITTER CONFIGURATION

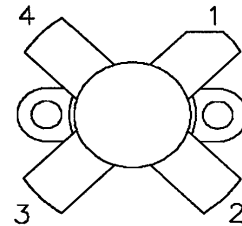


.500 4LFL (M174)
epoxy sealed

DESCRIPTION:

The MS1051 is a 12.5 V Class C epitaxial silicon NPN planar transistor designed primarily for HF communications. This device utilizes state-of-the-art diffused emitter ballasting to achieve extreme ruggedness under severe operating conditions.

PIN CONNECTION



1. Collector 3. Base
2. Emitter 4. Emitter

ABSOLUTE MAXIMUM RATINGS (T_{case} = 25°C)

Symbol	Parameter	Value	Unit
V _{CBO}	Collector-Base Voltage	36	V
V _{CEO}	Collector-Emitter Voltage	18	V
V _{EBO}	Emitter-Base Voltage	4.0	V
I _C	Device Current	20	A
P _{DISS}	Power Dissipation	290	W
T _J	Junction Temperature	+200	°C
T _{STG}	Storage Temperature	-65 to +150	°C

THERMAL DATA

R _{TH(J-C)}	Thermal Resistance Junction-case	0.6	°C/W
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Revision B, January 2010

ELECTRICAL SPECIFICATIONS (T_{case} = 25°C)
STATIC

Symbol	Test Conditions	Value			Unit
		Min.	Typ.	Max.	
BV_{CBO}	I_C = 100mA I_E = 0mA	36	---	---	V
BV_{CES}	I_C = 100mA V_{BE} = 0V	36	---	---	V
BV_{CEO}	I_C = 100mA I_B = 0mA	18	---	---	V
BV_{EBO}	I_E = 20mA I_C = 0mA	4.0	---	---	V
I_{CES}	V_{CE} = 15V I_C = 0mA	---	---	20	mA
h_{FE}	V_{CE} = 5V I_C = 5mA	10	---	200	---

DYNAMIC

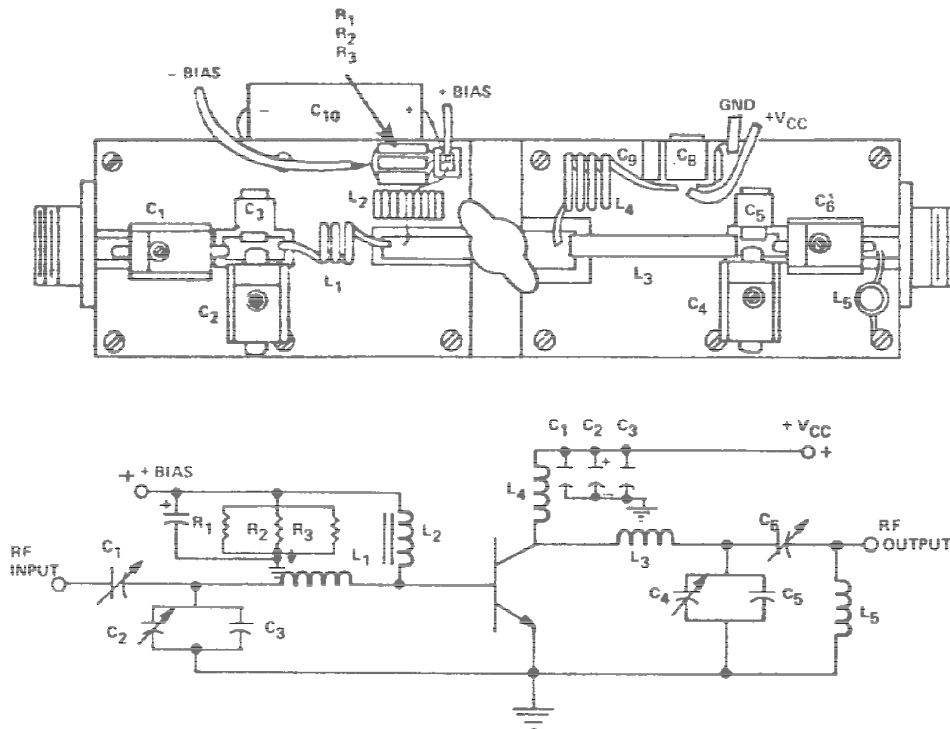
Symbol	Test Conditions	Value			Unit
		Min.	Typ.	Max.	
P_{OUT}	f = 30 MHz V_{CE} = 12.5 V I_{CQ} = 150mA	100	---	---	W
G_P	f = 30 MHz V_{CE} = 12.5 V I_{CQ} = 150mA	11	13	---	dB
IMD₃*	P_{OUT} = 100 W PEP V_{CE} = 12.5 V I_{CQ} = 150mA	---	---	-30	dBc
C_{OB}	f = 1 MHz V_{CB} = 12.5 V	---	400	---	pf

Conditions: f1 = 30.000MHz f2 = 30.001MHz

IMPEDANCE DATA

FREQ	$Z_{IN}(\Omega)$	$Z_{CL}(\Omega)$
30 MHz	$0.57 + j 0.78$	$0.80 + j 0.43$

$P_{OUT} = 100$ WPEP, $V_{CE} = 12.5$ V

TEST CIRCUIT


C1 : 9 - 180pF Arco 463
 C2 : 5 - 380pF Arco 465
 C3 : 200pF Arco 465
 C4, C6 : 170pF Arco 469
 C7 : 0.1 μ F Ceramic Disc
 C5, C8 : 1000pF Unelco
 C9 : 10 μ F Electrolytic, 35Vdc
 C10 : 1000 μ F Electrolytic, 35Vdc

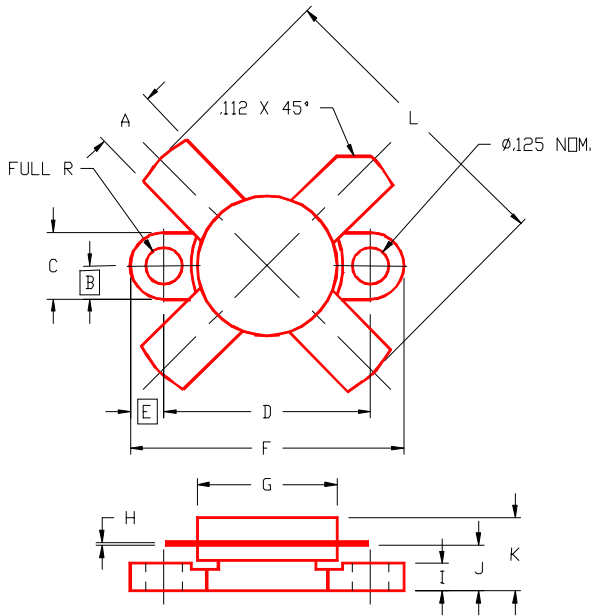
L3 : Copper Strap 1/4" Widht, Length 1 1/2, Height 1/2"
 L4 : 4 Turns, #16 AWG, Enameled Wire 3/8" I.D.
 L5 : 5 Turns, #18 AWG on 1/4" I.D. Coil Form Length 1/2", Ferrite Slug

R1, R2, R3 : 1.5 Ohm, 1 Watt Carbon

L1 : 2 1/2 Turns, #14 AWG, I.D. Loose Wound
 L2 : 16 Turns, #16 AWG, Enameled Wire on Micrometals Torroid #T-94

MS1051

PACKAGE MECHANICAL DATA



PACKAGE STYLE M174

	MINIMUM INCHES/MM	MAXIMUM INCHES/MM		MINIMUM INCHES/MM	MAXIMUM INCHES/MM
A	.220/5,59	.230/5,84	I	.090/2,29	.110/2,79
B	.125/3,18		J	.160/4,06	.175/4,45
C	.245/6,22	.255/6,48	K		.280/7,11
D	.720/18,28	.730/18,54	L		1.050/26,67
E	.125/3,18				
F	.970/24,64	.980/24,89			
G	.495/12,57	.505/12,83			
H	.003/0,08	.007/0,18			